Elektronische Bauelemente

2N3906

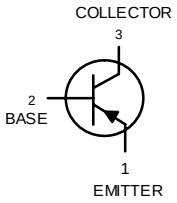
PNP Silicon

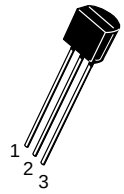
General Purpose Transistor

RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

TO-92





●FEATURES

- Power Dissipation
  P_{CM}: 625 mW (Ta=25℃)
- Collector Current
  I_{CM}: -200 mA
- Collector - Base Voltage
  $V_{(BR)CBO}$: -40 V

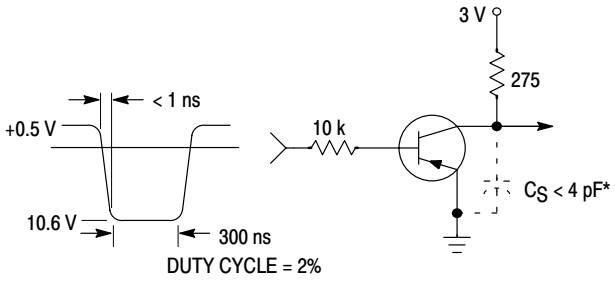
●ELECTRICAL CHARACTERISTICS (T_A = 25 ℃ unless otherwise specified)

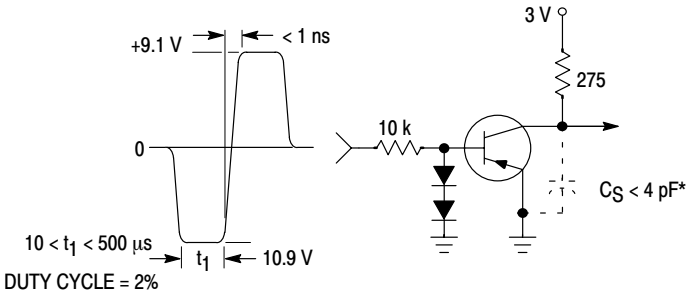
Parameter	SYMBOL	TEST CONDITIONS	Min.	Typ.	Max.	UNIT
Collector - Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = -1 mA, I_B = 0 A	-40	-	-	V
Collector - Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = -100 µA, I_E = 0 A	-40	-	-	V
Emitter - Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = -100 µA, I_C = 0 A	-5	-	-	V
Collector Cut-Off Current	I_{CBO}	V_{CB} = -40 V, I_E = 0 A	-	-	-0.1	µA
Collector Cut-Off Current	I_{CEO}	V_{CE} = -40 V, I_B = 0 A	-	-	-0.1	
Emitter Cut-Off Current	I_{EBO}	V_{EB} = -5 V, I_C = 0 A	-	-	-0.1	
DC Current Gain	$h_{FE(1)}$	V_{CE} = -1 V, I_C = -10 mA	100	-	400	-
	$h_{FE(2)}$	V_{CE} = -1 V, I_C = -50 mA	60	-	-	
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = -50 mA, I_B = -5 mA	-	-	0.3	V
Base - Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = -50 mA, I_B = -5 mA	-	-	-0.95	V
Transition Frequency	f_T	V_{CE} = -20 V, I_C = -10 mA f = 100 MHz	250	-	-	MHz
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-	-55 ~ +150			℃

●CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	G
Rang	100 ~ 200	200 ~ 300	300 ~ 400

●TYPICAL CHARACTERISTICS

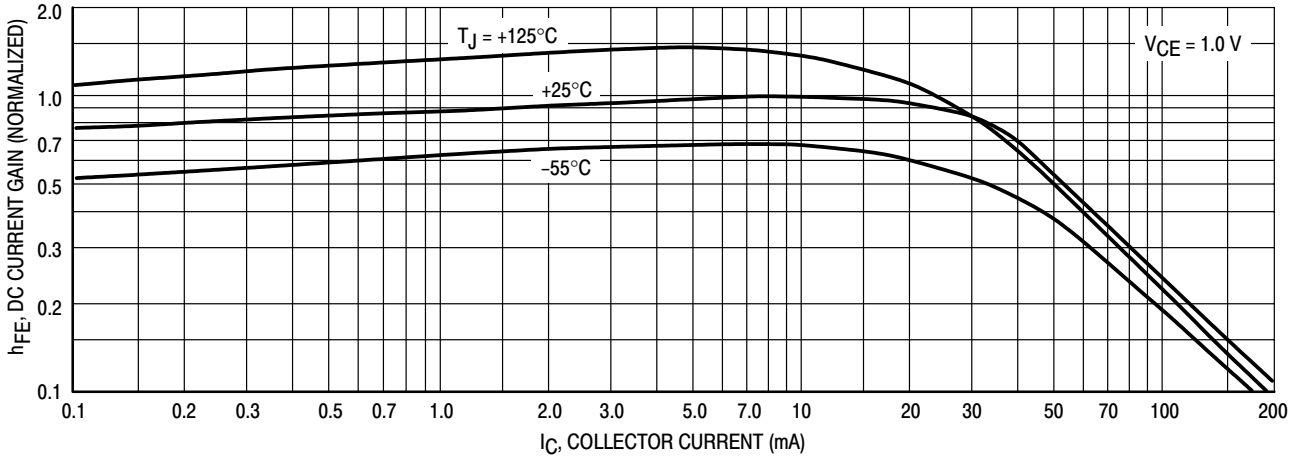




* Total shunt capacitance of test jig and connectors

Delay and Rise Time
Equivalent Test Circuit

Storage and Fall Time
Equivalent Test Circuit



DC Current Gain

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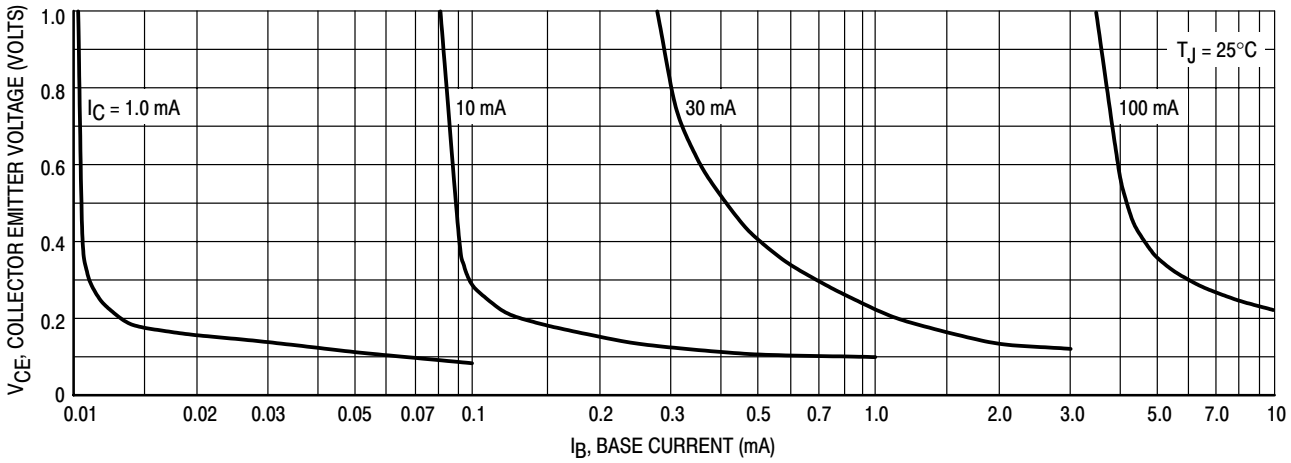
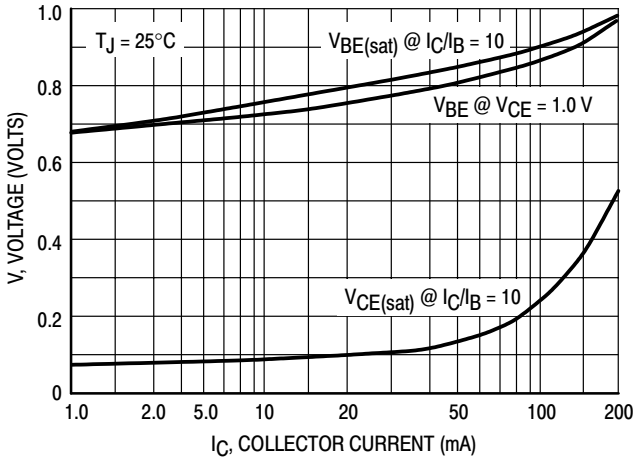
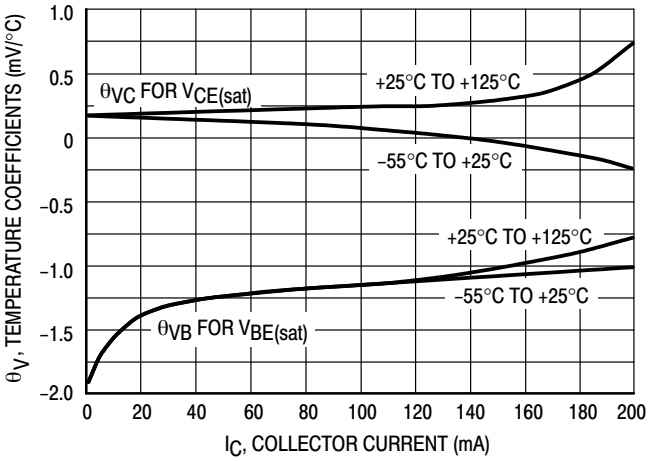


Collector Saturation Region



"ON" Voltages



Temperature Coefficients